

TSM9409

60V P-Channel MOSFET



SOP-8

Pin Definition:

Source
 Source
 Drain
 Source
 Drain

4. Gate 5. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
-60	155 @ V _{GS} = -10V	-3.5	
	200 @ V _{GS} = 4.5V	-3.1	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

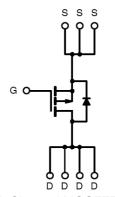
- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing		
TSM9409CS RLG	SOP-8	2.5Kpcs / 13" Reel		

Note: "G" denote for Halogen Free Product

Block Diagram



P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	-60	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		I _D	-3.5	А	
Pulsed Drain Current		I _{DM}	-30	А	
Continuous Source Current (Diode Conduction) ^{a,b}		I _S	-2.5	А	
Maximum Power Dissipation	T _A = 25°C	- P _D	3.0	W	
	T _A = 70°C		2.1		
Operating Junction Temperature		T_J	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R\Theta_{JC}$	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	50	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 10$ sec.





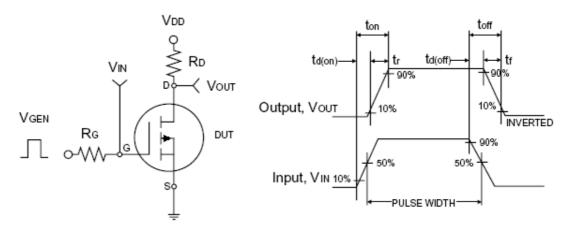
60V P-Channel MOSFET

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	V _{GS(TH)}	-1.0			V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -60V, V_{GS} = 0V$	I _{DSS}			-1.0	μA
On-State Drain Current ^a	V _{DS} =-5V, V _{GS} = -10V	I _{D(ON)}	-20			Α
Drain-Source On-State Resistance ^a	$V_{GS} = -10V, I_D = -3.5A$	_		125	155	mΩ
	$V_{GS} = -4.5V, I_D = -3.1A$	R _{DS(ON)}		153	200	
Forward Transconductance ^a	$V_{DS} = -15V, I_{D} = -3.5A$	g _{fs}		8		S
Diode Forward Voltage	I _S = -2.5A, V _{GS} = 0V	V _{SD}		-1.25	-1.5	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = -15V, I_{D} = -3.5A,$ $V_{GS} = -10V$	Qg		6		
Gate-Source Charge		Q _{gs}		1.7		nC
Gate-Drain Charge		Q_{gd}		1.5		
Input Capacitance	$V_{DS} = -30V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}		540		
Output Capacitance		C _{oss}		60		pF
Reverse Transfer Capacitance		C _{rss}		30		
Switching ^c						
Turn-On Delay Time	$V_{DD} = -15V, R_{L} = 15\Omega,$ $I_{D} = -1A, V_{GEN} = -10V,$ $R_{G} = 6\Omega$	t _{d(on)}		7		
Turn-On Rise Time		t _r		9		0
Turn-Off Delay Time		t _{d(off)}		19		nS
Turn-Off Fall Time		t _f	-	4	-	

Notes:

- a. pulse test: PW \leq 300 μ S, duty cycle \leq 2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

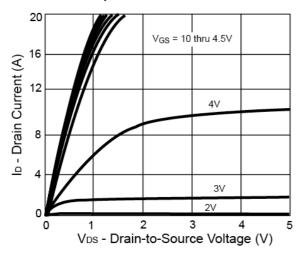
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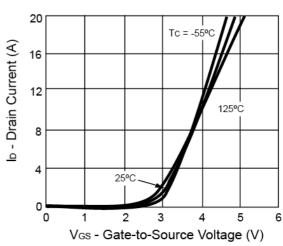


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

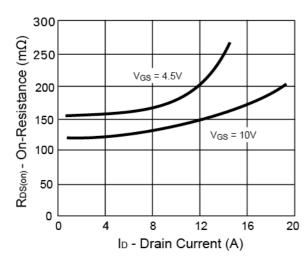
Output Characteristics



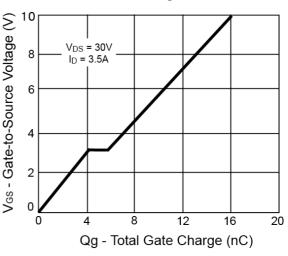
Transfer Characteristics



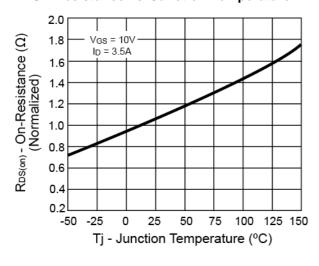
On-Resistance vs. Drain Current



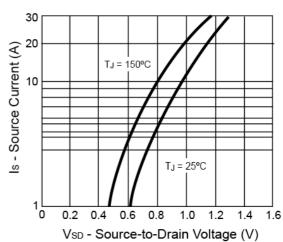
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



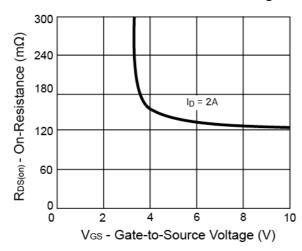




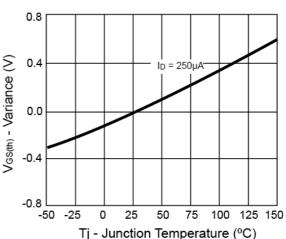


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

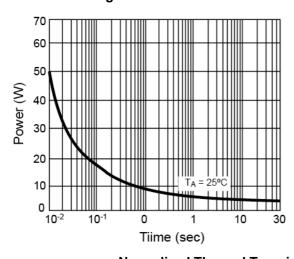
On-Resistance vs. Gate-Source Voltage



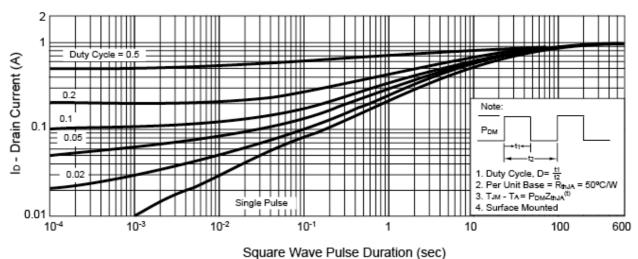
Threshold Voltage



Single Pulse Power



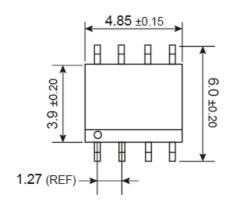
Normalized Thermal Transient Impedance, Junction-to-Ambient

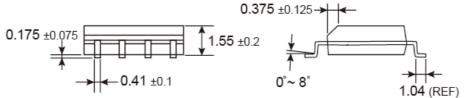






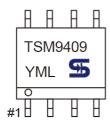
SOP-8 Mechanical Drawing





Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S = May T = Jun U = Jul V = Aug

 $W = Sep \quad X = Oct \quad Y = Nov \quad Z = Dec$

L = Lot Code



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Document Number: DS_P0000153 7 Version: C15

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